



AIM: To STUDY INPUT/OUTPUT CHARACTERISTICS OF A NPN COMMON EMITTER TRANSISTOR.

REQUIREMENTS:

Transistor, Bread board, Resistors, Connecting wires, DC power supply, multimeters

THEORY:

The transistor is a two junction, three terminal semiconductor device which has three regions namely the emitter region, the base region, and the collector region. There are two types of transistors - npn and pnp.

An npn transistor has an n-type emitter, a p-type base and an n-type collector. A pnp transistor has a p-type emitter, an n-type base and a p-type collector.

The emitter is heavily doped, base region is thin and lightly doped, and collector is moderately doped and is the largest. The current conduction in transistors takes place due to both the charge carriers - that is electrons and holes, and hence, they are also called as Bipolar Junction Transistors.

For npn-transistor, input characteristic is the curve between input current  $I_b$  and input voltage  $V_{be}$  for some constant collector emitter voltage  $V_{ce}$ . Similarly, output characteristic shows the relation between collector

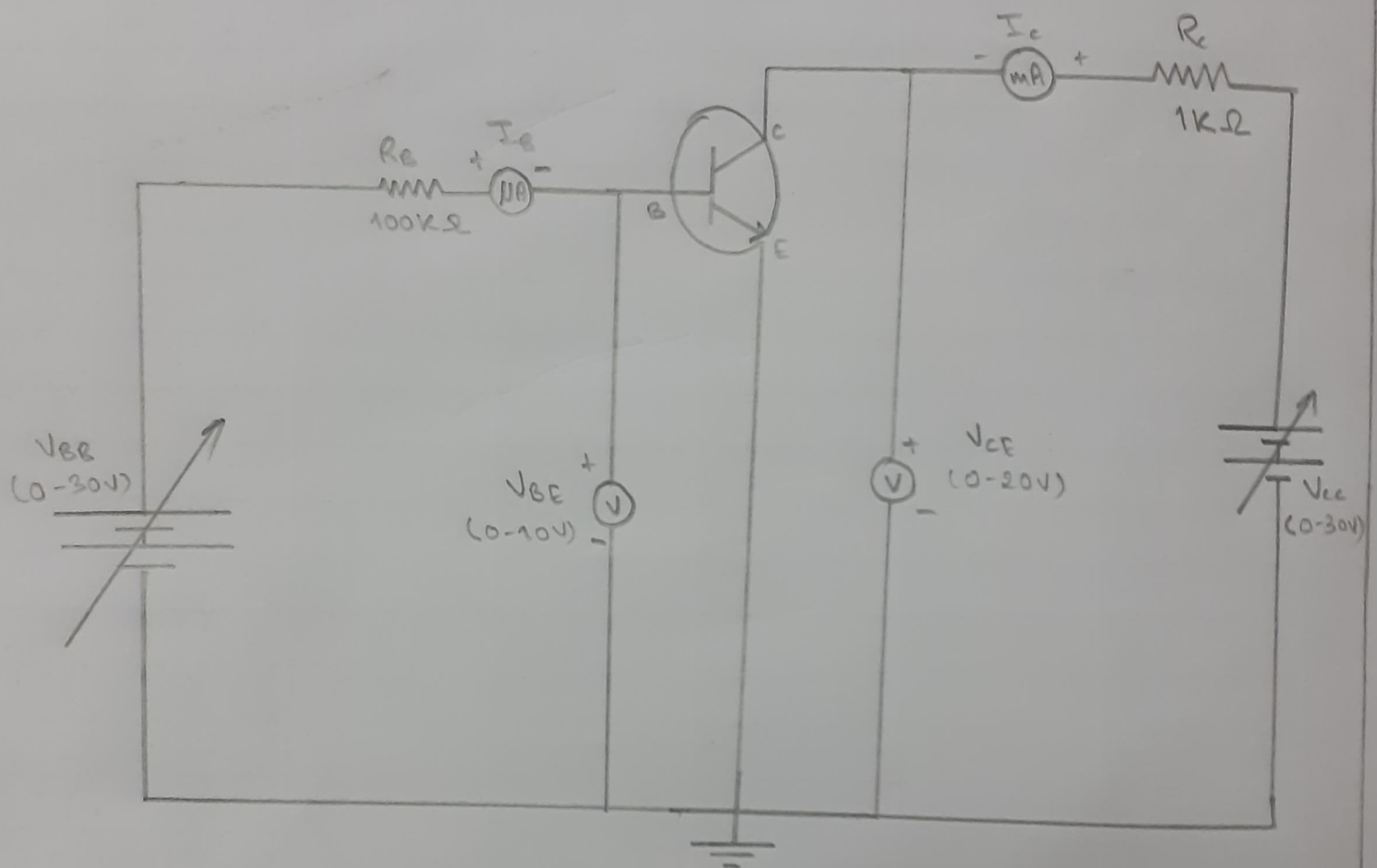


fig.: Circuit Diagram of npn-Transistor

current  $I_c$  and collector voltage  $V_{ce}$  for various constant values of  $I_B$ .

### PROCEDURE :

- i) The circuit was made as per the circuit diagram.
- ii) For input characteristics; the forward bias voltage was applied on base junction.
- iii) The base voltage,  $V_{BE}$  and base current,  $I_B$  were read and noted.
- iv)  $V_{BE}$  was kept on increasing until  $I_B$  value raised suddenly.
- v) The corresponding values of  $I_B$  for each value of  $V_{BE}$  were noted.
- vi) For output characteristics, the collector voltage,  $V_{ce}$  and the collector current,  $I_c$  were noted for every value variation in  $V_{ce}$ , while keeping  $I_B$  constant.
- vii) The obtained values were noted and the graph was plotted accordingly.



## OBSERVATION TABLE

## INPUT CHARACTERISTICS

$V_{BB}$ (in V)	$V_{CE} = 2V$		$V_{CE} = 0V$	
	$V_{BE}$ (V)	$I_B$ ( $\mu A$ )	$V_{BE}$ (V)	$I_B$ ( $\mu A$ )
2.8	0.15	0.14	0.14	0.1
6.6	0.43	0.50	0.43	0.6
7.8	0.44	0.70	0.44	0.7
8.4	0.45	0.80	0.45	0.8
10.5	0.46	1.00	0.45	1.0
12.2	0.46	1.20	0.46	1.3
14.4	0.47	1.40	0.47	1.5

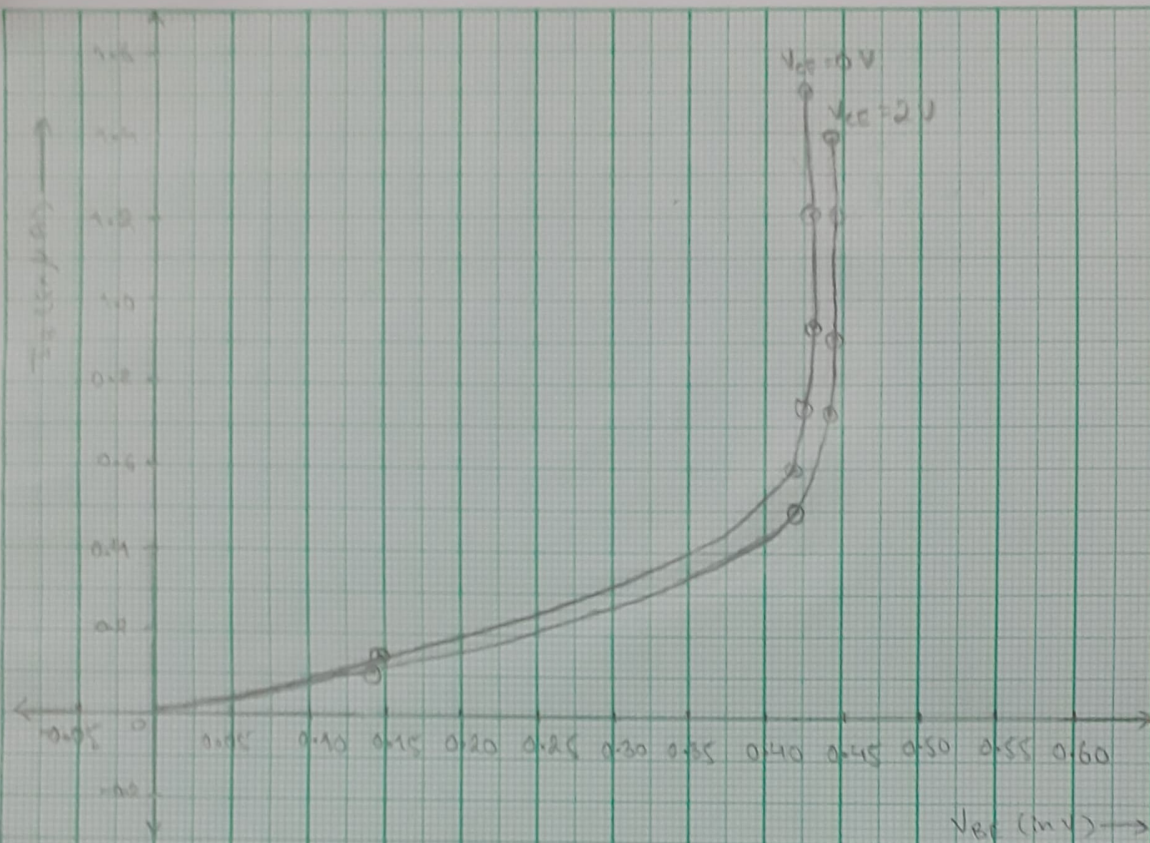
## OUTPUT CHARACTERISTICS

$V_{BB}$ (in V)	$I_B = 0 \mu A$		$I_B = 20 \mu A$	
	$V_{CE}$ (V)	$I_C$ (mA)	$V_{CE}$ (in V)	$I_C$ (mA)
2.8	0.1	0.440	0.1	0.702
6.6	0.2	0.520	0.2	1.281
7.8	0.4	0.601	0.4	1.812
8.4	0.5	0.602	0.5	1.907
10.5	0.6	0.604	0.6	1.911
12.2	0.8	0.608	0.8	1.914
14.4	1.0	0.610	1.0	1.918

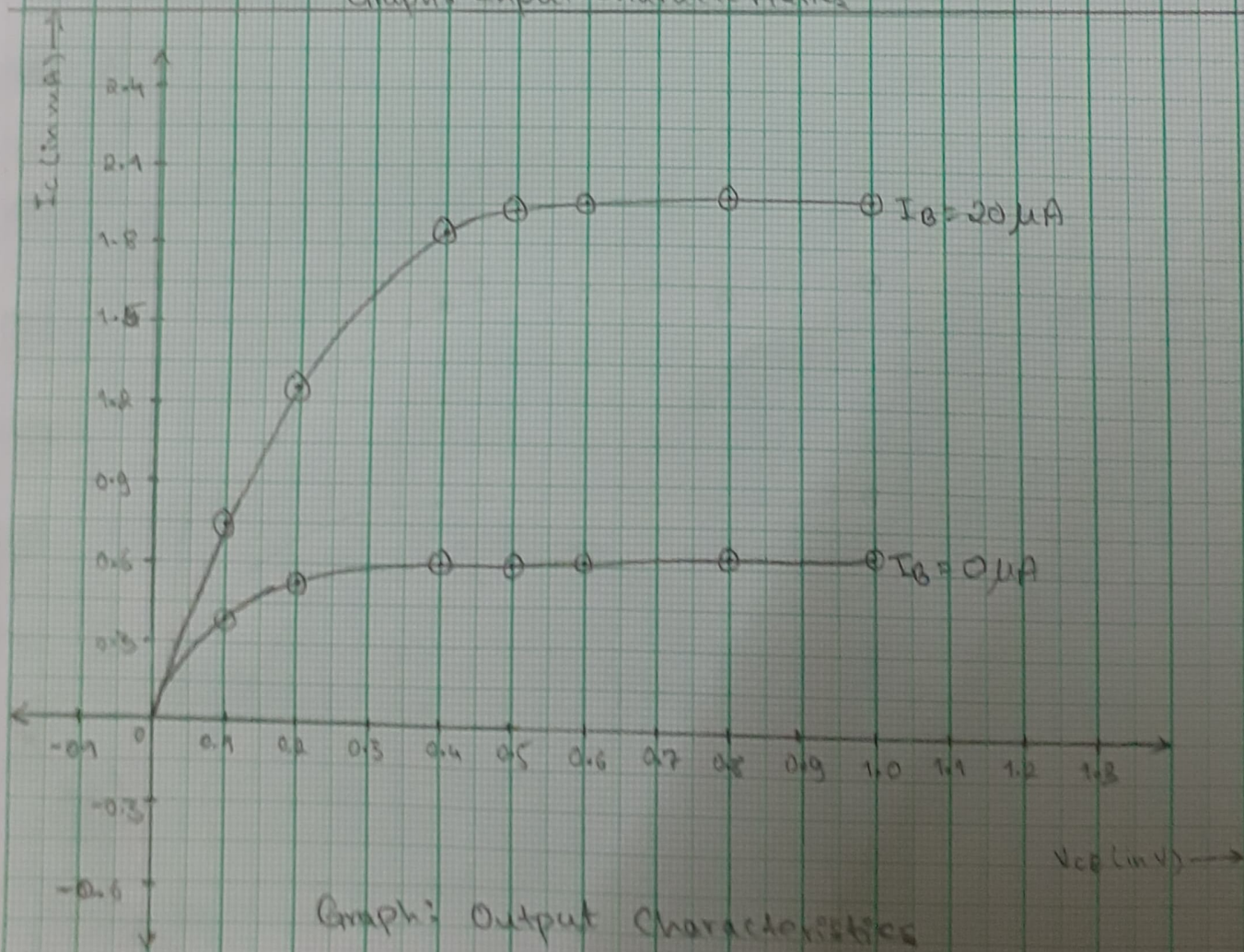
## CONCLUSION:

The input and output characteristics of a npn common emitter transistor were studied.





Graph: Input characteristics



Graph: Output characteristics